

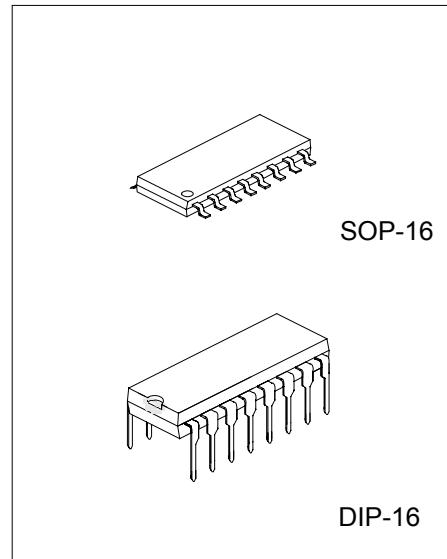
ANALOG MULTIPLEXERS /DEMULTIPLEXERS

DESCRIPTION

The UTC 4052 analog multiplexers is digitally controlled analog switch. The device feature low ON impedance and very low OFF leakage current. Control of analog signals up to the complete supply voltage range can be achieved.

FEATURES

- *Triple Diode Protection on Control Inputs
- *Switch Function is Break Before Make
- *Supply Voltage Range=3.0 Vdc to 18 Vdc
- *Analog Voltage Range(VDD-VEE)=3.0 to 18V
- Note: VEE must be \leq Vss
- *Linearized Transfer Characterisstics
- *Low-noise- $12\text{nV}/\sqrt{\text{Cycle}}$, $f \geq 1.0\text{kHz}$ Typical

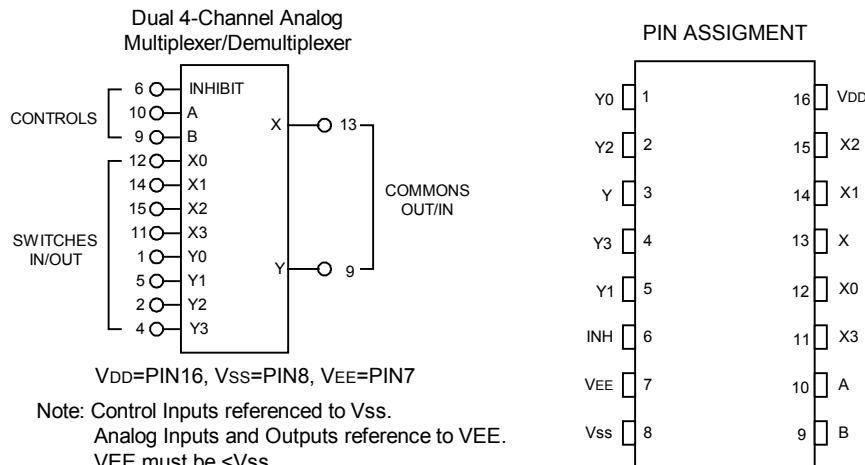


ABSOLUTE MAXIMUM RATINGS^{*1}

PARAMETER	SYMBOL	RATING	UNIT
DC Supply Voltage (Referenced to VEE,Vss \geq VEE)	V _{DD}	-0.5 ~ +18.0	V
Input or Output Voltage (DC or Transient) (Referenced to Vss for Control Inputs and VEE for switch I/O)	V _{in} ,V _{out}	-0.5 ~ V _{DD} +0.5	V
Input Current (DC or Transient) per Control Pin	I _{in}	± 10	mA
Switch Through Current	I _{sw}	± 25	mA
Power Dissipation ^{*2} DIP-16 SOP-16	P _D	700 500	mW
Ambient Temperature Range	T _A	-55 ~ +125	°C
Storage Temperature Range	T _{stg}	-65 ~ +150	°C
Lead Temperature (8-Second Soldering)	T _{LEAD}	260	°C

*1. Maximum Ratings are those values beyond which damage to the device may occur.

*2. Temperature Derating : 7.0 mW/°C From 65°C ~ 125°C

**ELECTRICAL CHARACTERISTICS**

PARAMETER	SYMBOL	TEST CONDITIONS	-55°C		25°C		125°C		UNIT	
			MIN	MAX	MIN	TYP ³	MAX	MIN		
SUPPLY REQUIREMENTS (Voltages Referenced to VEE)										
Power Current Per Range	V _{DD}	V _{DD} -3.0 ≥ V _{ss} ≥ V _{EE}	3.0	18	3.0		18	3.0	18	V
Quiescent Current Per Package	I _{DD}	Control Inputs: Vin=Vss or V _{DD} , Switch I/O : V _{EE} ≤ V _{i/o} ≤ V _{DD} , and ΔV _{switch} ≤ 500mV ^{*4} V _{DD} =5.0V V _{DD} =10V V _{DD} =15V			5.0 10 20	0.005 0.010 0.015	5.0 10 20	150 300 600	μA	
Total Supply Current (Dynamic Plus Quiescent, Per Package)	I _{D(AV)}	TA=25°C only (The channel component, (Vin-Vout)/Ron, is not included.) V _{DD} =5.0V V _{DD} =10V V _{DD} =15V			Typical (0.07μA/kHz)f+I _{DD} (0.20μA/kHz)f+I _{DD} (0.36μA/kHz)f+I _{DD}				μA	
CONTROL INPUTS-INHIBIT, A, B, C (Voltages Referenced to Vss)										
Low-Level Input Voltage	V _{IL}	Ron=per spec, loff=per spec V _{DD} =5.0V V _{DD} =10V V _{DD} =15V			1.5 3.0 4.0	2.25 4.50 6.75	1.5 3.0 4.0	1.5 3.0 4.0	V	
High-Level Input Voltage	V _{IH}	Ron=per spec, loff=per spec V _{DD} =5.0V V _{DD} =10V V _{DD} =15V	3.5 7.0 11	3.5 7.0 11	2.75 5.50 8.25		3.5 7.0 11	- - -	V	

UTC 4052 CMOS

PARAMETER	SYMBOL	TEST CONDITIONS	-55°C		25°C		125°C		UNIT
			MIN	MAX	MIN	TYP ^{*3}	MAX	MIN	
Input Leakage Current	Iin	V _{DD} =15V , V _{in} =0 or V _{DD}		±0.1		±10 ⁻⁵	±0.1		1.0 μA
Input Capacitance	C _{in}				5.0	7.5			pF
SWITCHES IN/OUT AND COMMONS OUT/IN -X,Y,Z(Voltages Referenced to VEE)									
Recommended Peak-to-Peak Voltage Into or Out of the Switch	V _{i/o}	Channel On or Off	0	V _{DD}	0		V _{DD}	0	V _{DD} V _{pp}
Recommended Static or Dynamic Voltage Across the Switch ^{*4} (Figure 3)	△V _{switch}	Channel On	0	600	0		600	0	300 mV
Output Offset Voltage	V _{oo}	V _{in} =0V, No Load			10				μV
ON Resistance	R _{on}	△V _{switch} ≤500mV ^{*4} V _{in} =V _{IL} or V _{IH} (Control), and V _{in} =0 to V _{DD} (Switch) V _{DD} =5.0V V _{DD} =10V V _{DD} =15V		800 400 220		250 120 80	1050 500 280	1200 520 300	Ω
△ON Resistance Between Any Two Channels in the Same Package	△R _{on}	V _{DD} =5.0V V _{DD} =10V V _{DD} =15V		70 50 45		25 10 10	70 50 45	135 95 65	Ω
Off-Channel Leakage Current(Figure 8)	I _{off}	V _{DD} =15V , V _{in} =V _{IL} or V _{IH} (Control) Channel to Channel or Any One Channel		±100		±0.05	±100	±1000	nA
Capacitance, Switch I/O	C _{i/o}	Inhibit=V _{DD}			10				pF
Capacitance, Common O/I	C _{o/i}	Inhibit=V _{DD}			32				pF
Capacitance, Feedthrough (Channel Off)	C _{i/o}	Pins Not Adjacent Pins Adjacent			0.15 0.47				pF

*3. Data labeled "Typ" is not to be used for design purposes, but is intended as an indication of the IC's potential performance.

*4. For voltage drops across the switch ($\triangle V_{switch}$) > 600 mV (> 300 mV at high temperature), excessive V_{DD} current may be drawn, i.e. the current out of the switch may contain both V_{DD} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded. (See first page of this data sheet.)

ELECTRICAL CHARACTERISTICS^{*5} ($C_L = 50 \text{ pF}$, $T_A = 25^\circ\text{C}$) ($V_{EE} \leq V_{SS}$ unless otherwise indicated)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP ^{*6}	MAX	UNIT
Propagation Delay Times(Figure 4) Switch Input to Switch Output	t_{PLH}, t_{PHL}	$R_L=10\text{k}\Omega$ $V_{DD}-V_{EE}=5.0$, $t_{PLH}, t_{PHL}=(0.17 \text{ ns/pF}) C_L+21.5 \text{ ns}$ $V_{DD}-V_{EE}=10$, $t_{PLH}, t_{PHL}=(0.08 \text{ ns/pF}) C_L+8.0 \text{ ns}$ $V_{DD}-V_{EE}=15$, $t_{PLH}, t_{PHL}=(0.06 \text{ ns/pF}) C_L+7.0 \text{ ns}$		30 12 10	75 30 25	ns
Propagation Delay Times(Figure 4) Inhibit to Output	t_{PHZ}, t_{PLZ} t_{PZH}, t_{PZL}	$R_L=10\text{k}\Omega, V_{EE}=V_{SS}$ Output "1" or "0" to High Impedance, or High Impedance to "1" or "0" Level $V_{DD}-V_{EE}=5.0$ $V_{DD}-V_{EE}=10$ $V_{DD}-V_{EE}=15$		300 155 125	600 310 250	ns
Propagation Delay Times(Figure 4) Control Input to Output	t_{PLN}, t_{PHL}	$R_L=10\text{k}\Omega, V_{EE}=V_{SS}$ $V_{DD}-V_{EE}=5.0$ $V_{DD}-V_{EE}=10$ $V_{DD}-V_{EE}=15$		325 130 90	650 260 180	ns
Second Harmonic Distortion		$R_L=10\text{k}\Omega, f=1\text{kHz}, V_{in}=5\text{Vpp}, V_{DD}-V_{EE}=10$		0.07		%
Bandwidth (Figure 5)	BW	$R_L=1\text{k}\Omega, V_{in}=1/2(V_{DD}-V_{EE})\text{p-p}, C_L=50\text{pF},$ 20 Log $(V_{out}/V_{in})=-3\text{dB}$, $V_{DD}-V_{EE}=10$		17		MHz
Off Channel Feedthrough Attenuation (Figure 5)		$R_L=1\text{k}\Omega, V_{in}=1/2(V_{DD}-V_{EE})\text{p-p}, f_{in}=30\text{MHz},$ $V_{DD}-V_{EE}=10$		-50		dB
Channel Separation (Figure 6)		$R_L=1\text{k}\Omega, V_{in}=1/2(V_{DD}-V_{EE})\text{p-p}, f_{in}=3.0\text{MHz},$ $V_{DD}-V_{EE}=10$		-50		dB
Crosstalk ,Control Input to Common O/I (Figure 7)		$R_1=1\text{k}\Omega, R_L=10\text{k}\Omega,$ Control $t_{TLH}=t_{THL}=20\text{ns}$, Inhibit= V_{SS} , $V_{DD}-V_{EE}=10$		75		mV

*5. The formulas given are for the typical characteristics only at 25 °C.

*6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

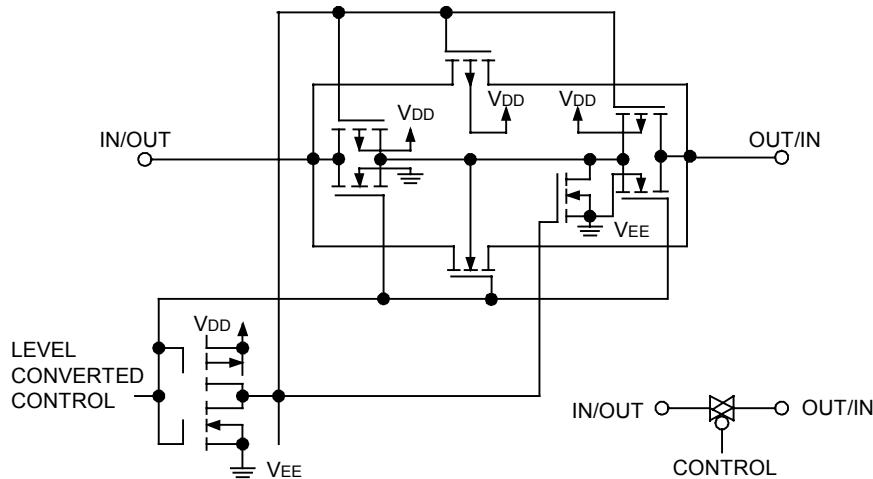


Figure 1.Switch Circuit Schematic

TRUTH TABLE		
Control Inputs		ON Switches
Inhibit	Select	
	B A	
0	0 0	Y0 X0
0	0 1	Y1 X1
0	1 0	Y2 X2
0	1 1	Y3 X3
1	X X	None

* X=Don't Care

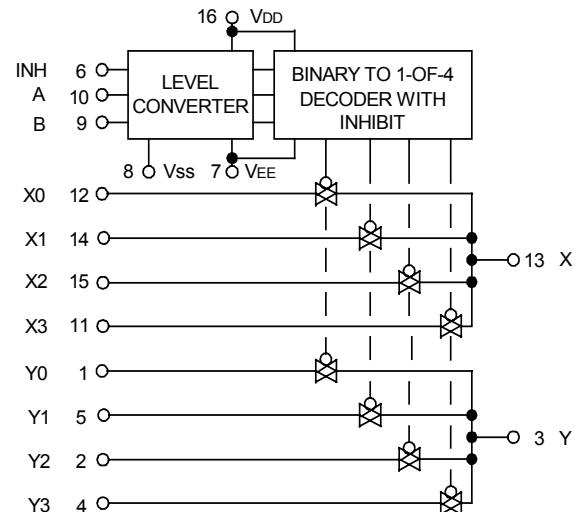


Figure 2. Functional Diagram

TEST CIRCUITS

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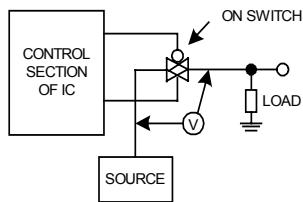


Figure 3. $\rightarrow \Delta V$ Across Switch

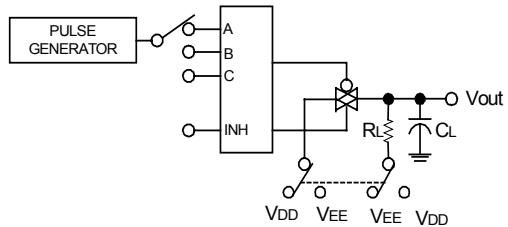


Figure 4. Propagation Delay Times, Control and Inhibit to Output

A,B, and C inputs used to turn ON or OFF the switch under test.

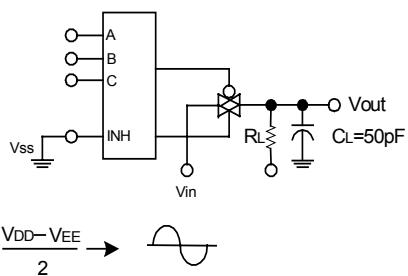


Figure 5. Bandwidth and Off-Channel Feedthrough Attenuation

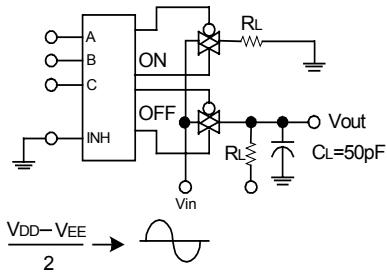


Figure 6. Channel Separation
(Adjacent Channels Used For Setup)

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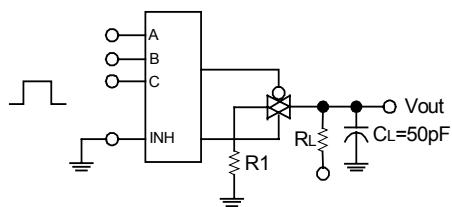


Figure 7. Crosstalk,Control Input to Common O/I

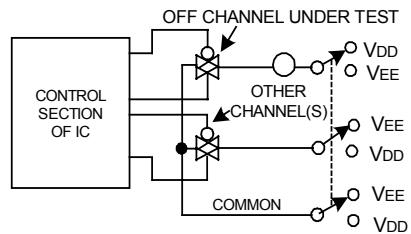


Figure 8. Off Channel Leakage

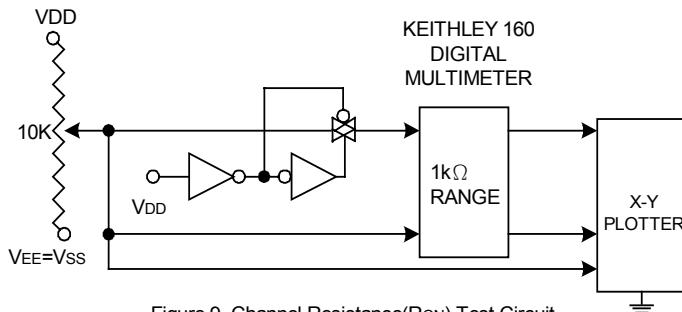


Figure 9. Channel Resistance(R_{ON}) Test Circuit

TYPICAL RESISTANCE CHARACTERISTICS

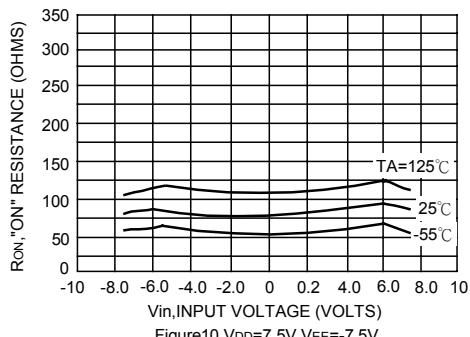


Figure10. $V_{DD}=7.5V, V_{EE}=-7.5V$

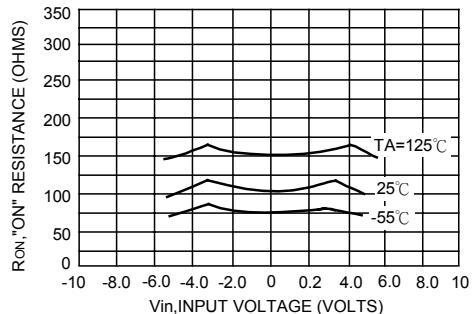


Figure11. $V_{DD}=5.0V, V_{EE}=-5.0V$

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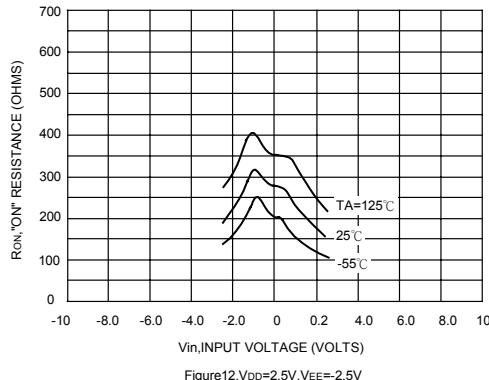


Figure 12. V_{DD}=2.5V, V_{EE}=-2.5V

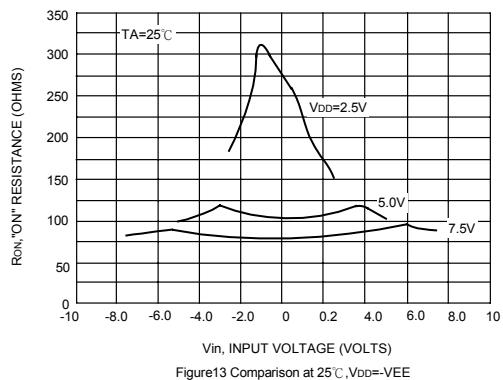


Figure 13 Comparison at 25°C, V_{DD}=-V_{EE}

Figure A illustrates use of the on-chip level converter detailed in Figures 2. The 0 ~ 5 V Digital Control signal is used to directly control a 9 Vp-p analog signal.

The digital control logic levels are determined by V_{DD} and V_{SS}. The V_{DD} voltage is the logic high voltage; the V_{SS} voltage is logic low. For the example, V_{DD} = + 5 V = logic high at the control inputs; V_{SS} = GND = 0 V = logic low.

The maximum analog signal level is determined by V_{DD} and V_{EE}. The V_{DD} voltage determines the maximum recommended peak above V_{SS}. The V_{EE} voltage determines the maximum swing below V_{SS}. For the example, V_{DD} – V_{SS} = 5 V maximum swing above V_{SS}; V_{SS} – V_{EE} = 5 V maximum swing below V_{SS}. The example shows a ± 4.5 V signal which allows a 1/2 volt margin at each peak. If voltage transients above V_{DD} and/or below V_{EE} are anticipated on the analog channels, external diodes (D_X) are recommended as shown in Figure B. These diodes should be small signal types able to absorb the maximum anticipated current surges during clipping.

The absolute maximum potential difference between V_{DD} and V_{EE} is 18.0 V. Most parameters are specified up to 15 V which is the recommended maximum difference between V_{DD} and V_{EE}.

Balanced supplies are not required. However, V_{SS} must be greater than or equal to V_{EE}. For example, V_{DD} = + 10 V, V_{SS} = + 5 V, and V_{EE} = - 3 V is acceptable. See the Table below.

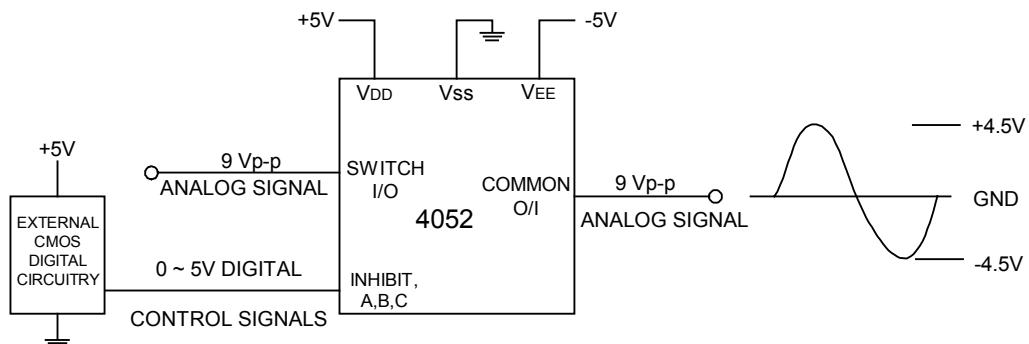


Figure A. Application Example

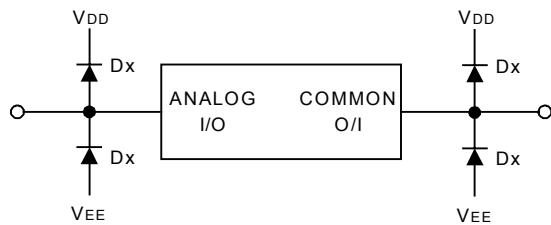


Figure B.External Germanium or Schottky Clipping Diodes

POSSIBLE SUPPLY CONNECTIONS

VDD IN VOLTS	VSS IN VOLTS	VEE IN VOLTS	CONTROL INPUTS LOGIC HIGH/LOGIC LOW IN VOLTS	MAXIMUM ANALOG SIGNAL RANGE IN VOLTS
+8	0	-8	+8/0	+8 ~ -8=16Vp-p
+5	0	-12	+5/0	+5 ~ -12=17Vp-p
+5	0	0	+5/0	+5 ~ 0=5Vp-p
+5	0	-5	+5/0	+5 ~ -5=10Vp-p
+10	+5	-5	+10/+5	+10 ~ -5=15Vp-p